

## N-Channel 150-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
150	0.030 at V <sub>GS</sub> = 10 V	50
	0.033 at V <sub>GS</sub> = 6 V	45

### FEATURES

- TrenchFET<sup>®</sup> Power MOSFETs
- 175 °C Junction Temperature
- New Low Thermal Resistance Package
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC

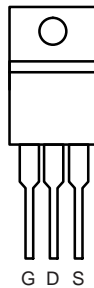


RoHS  
COMPLIANT

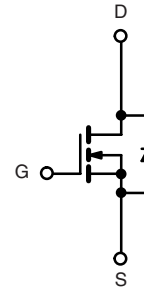
### APPLICATIONS

- Primary Side Switch

TO-220AB



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>C</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V <sub>DS</sub>	150	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20			
Continuous Drain Current (T <sub>J</sub> = 175 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	50	A	
		T <sub>C</sub> = 125 °C	35		
Pulsed Drain Current	I <sub>DM</sub>	150			
Avalanche Current	I <sub>AR</sub>	50			
Repetitive Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AR</sub>	80	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	166 <sup>b</sup>	W	
	T <sub>A</sub> = 25 °C <sup>c</sup>		3.75		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient <sup>c</sup>	R <sub>thJA</sub>	40	°C/W	
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.9		

Notes:

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).

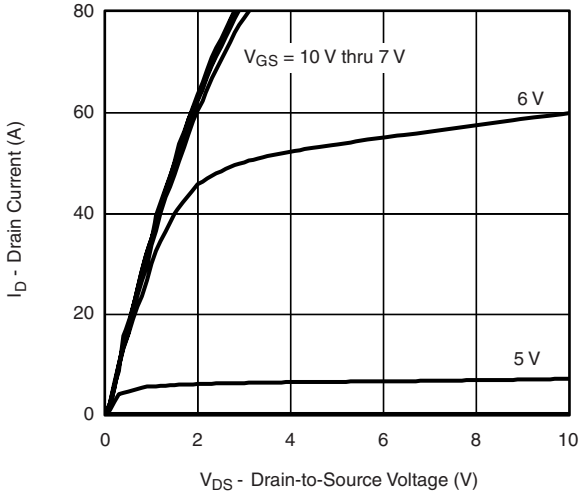
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 120\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	80			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		0.030		$\Omega$
		$V_{GS} = 6\text{ V}, I_D = 10\text{ A}$		0.033		
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.076		
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 175\text{ }^\circ\text{C}$		0.100		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$	10			S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2500		$\text{pF}$
Output Capacitance	$C_{oss}$			290		
Reverse Transfer Capacitance	$C_{rss}$			190		
Gate Resistance	$R_g$			2		$\Omega$
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 40\text{ A}$		38	60	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			13		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			13		
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 75\text{ V}, R_L = 1.80\text{ }\Omega$ $I_D \equiv 40\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		15	25	ns
Rise Time <sup>c</sup>	$t_r$			130	200	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			30	45	
Fall Time <sup>c</sup>	$t_f$			90	140	
<b>Source-Drain Diode Ratings and Characteristics <math>T_C = 25\text{ }^\circ\text{C}</math><sup>b</sup></b>						
Continuous Current	$I_S$				40	A
Pulsed Current	$I_{SM}$				80	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 40\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F = 40\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		100	150	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			5	8	A
Reverse Recovery Charge	$Q_{rr}$			0.25	0.6	$\mu\text{C}$

Notes:

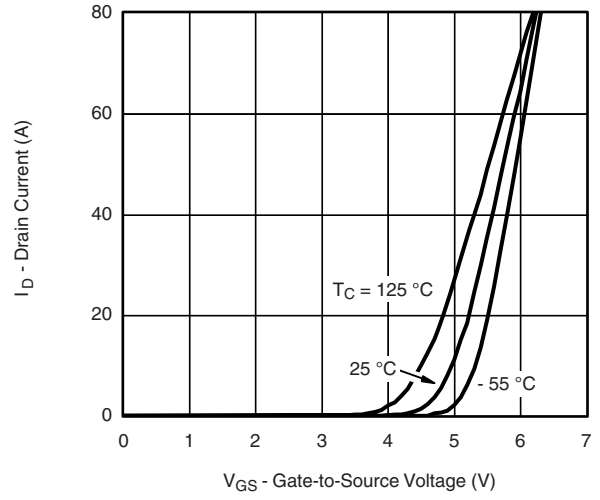
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

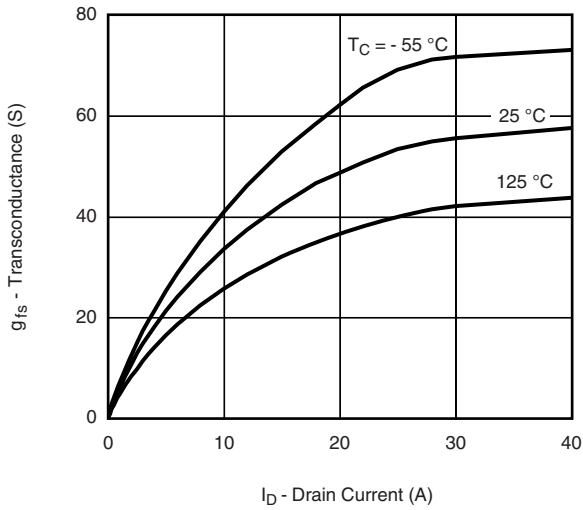
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



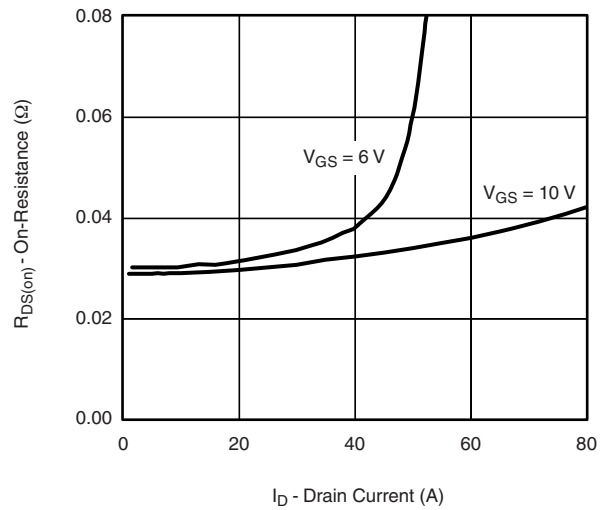
**Output Characteristics**



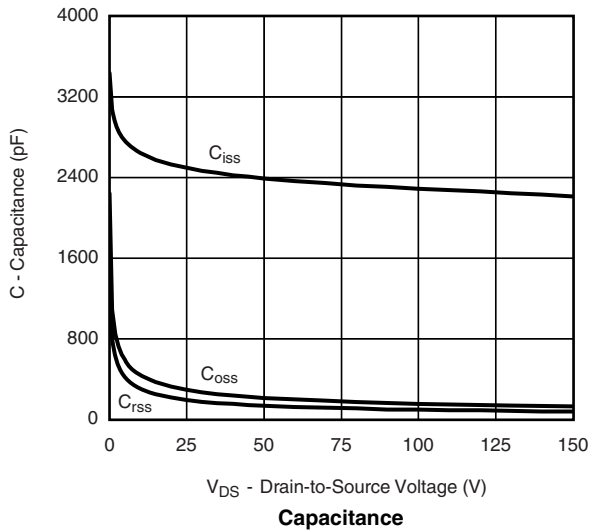
**Transfer Characteristics**



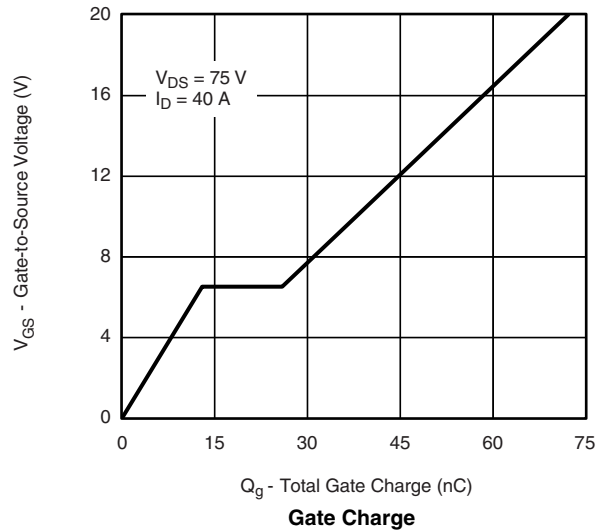
**Transconductance**



**On-Resistance vs. Drain Current**

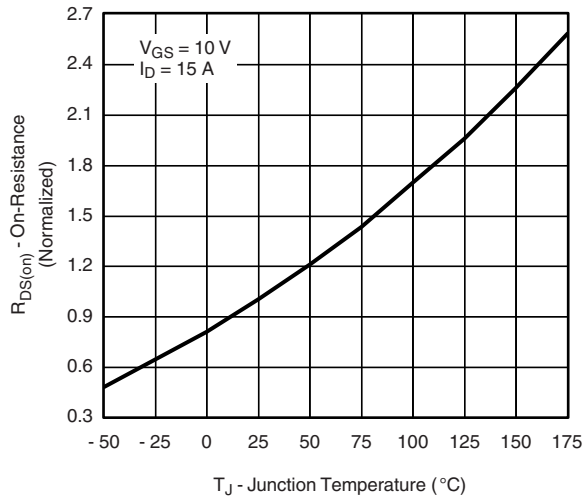


**Capacitance**

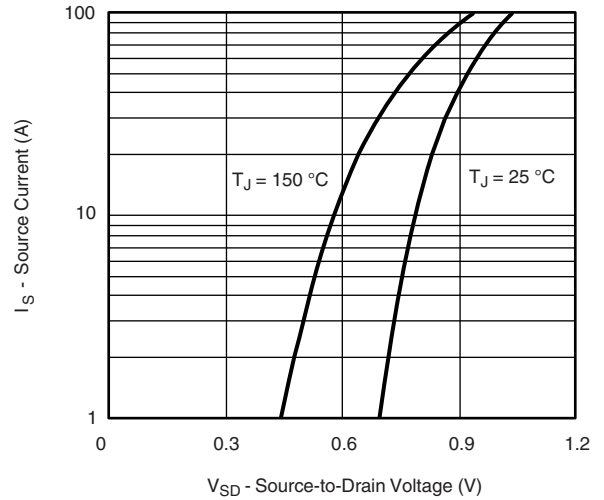


**Gate Charge**

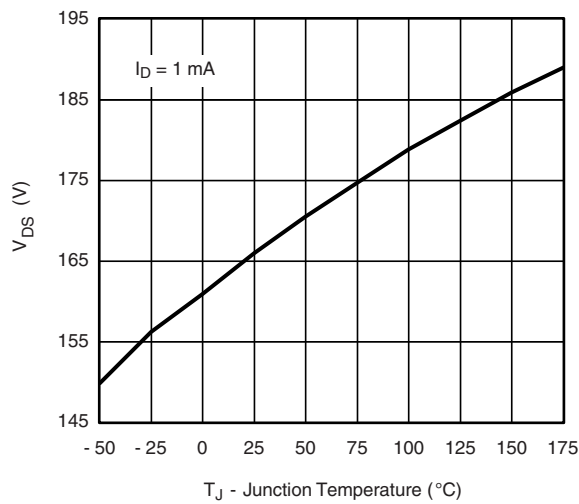
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**On-Resistance vs. Junction Temperature**

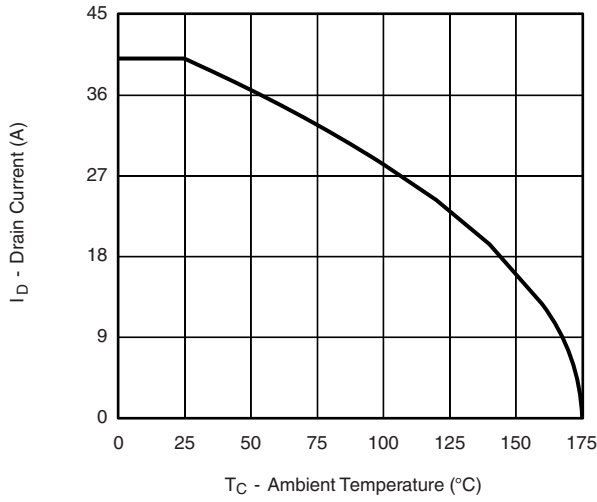


**Source-Drain Diode Forward Voltage**

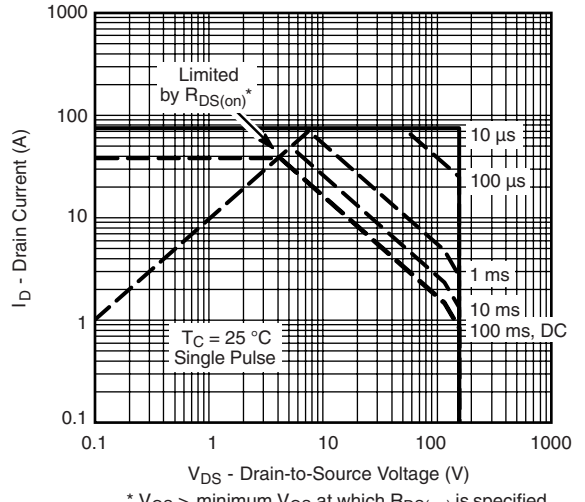


**Drain Source Breakdown vs. Junction Temperature**

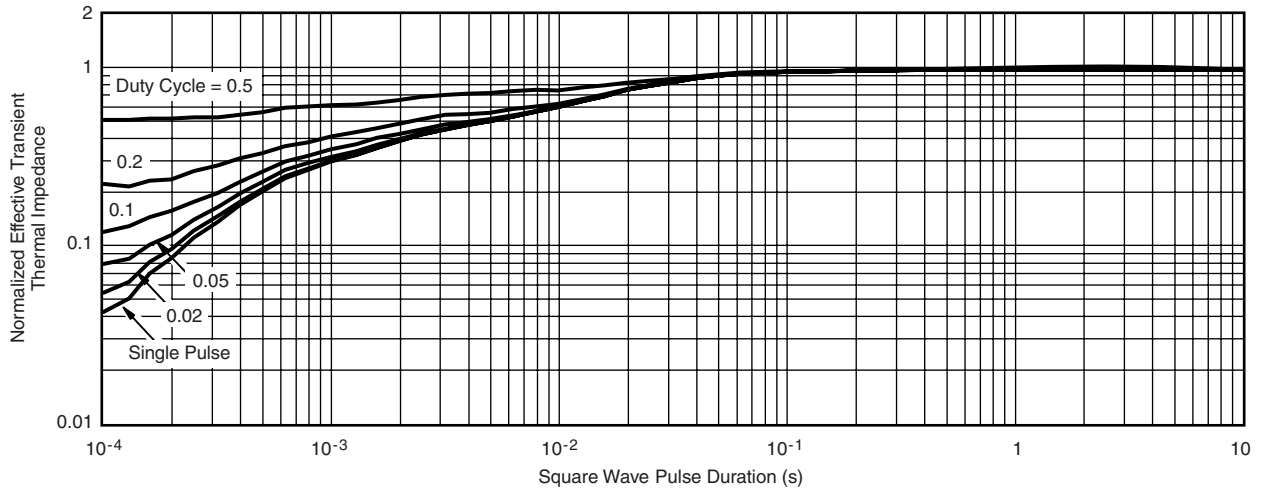
**THERMAL RATINGS**



**Maximum Avalanche and Drain Current vs. Case Temperature**

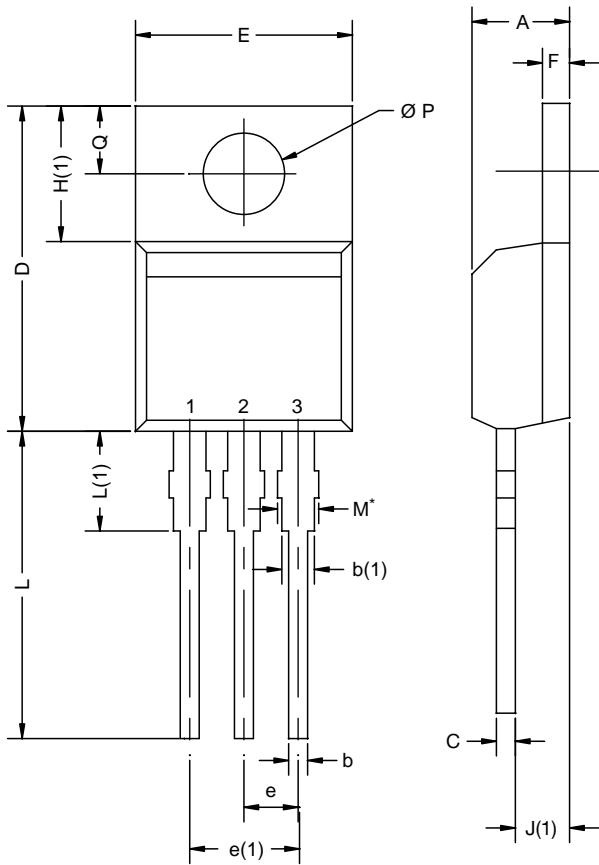


**Safe Operating Area**  
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



**Normalized Thermal Transient Impedance, Junction-to-Case**

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12  
DWG: 5471

**Notes**  
\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM

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